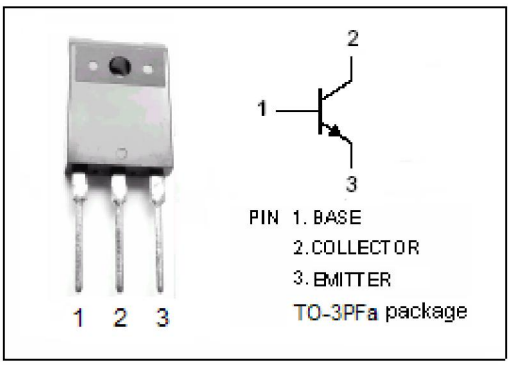
isc Silicon NPN Power Transistor BUW12F

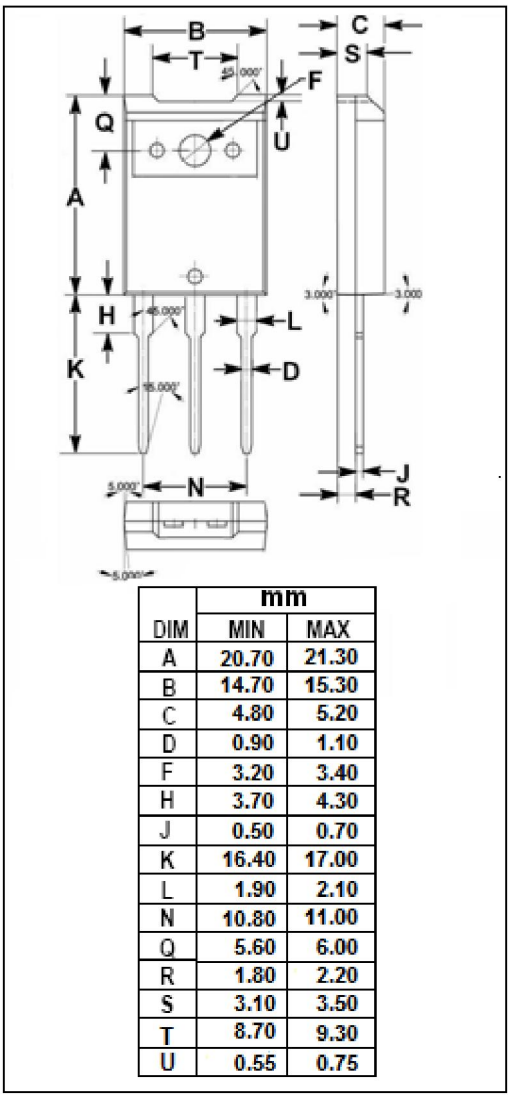
DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 400V(Min.)
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= 1.5V(Max.)@I_C= 6A
- High Speed Switching

APPLICATIONS

- Designed for high voltage, fast switching industrial applications.





DIM	mm MIN	MAX
A	20.70	21.30
B	14.70	15.30
C	4.80	5.20
D	0.90	1.10
F	3.20	3.40
H	3.70	4.30
J	0.50	0.70
K	16.40	17.00
L	1.90	2.10
N	10.80	11.00
Q	5.60	6.00
R	1.80	2.20
S	3.10	3.50
T	8.70	9.30
U	0.55	0.75

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	850	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current-Continuous	8	A
I_{CM}	Collector Current-Peak	20	A
I_B	Base Current	4	A
I_{BM}	Base Current-Peak	6	A
P_C	Collector Power Dissipation @T_C=25℃	34	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	3.7	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 0.1A; I_B= 0, L= 25mH	400			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 6A; I_B= 1.2A			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 6A; I_B= 1.2A			1.5	V
I_{CES}	Collector Cutoff Current	V_{CE}=V_{CES} ;V_{BE}= 0 V_{CE}=V_{CES} ;V_{BE}= 0;T_C=125℃			1.0 3.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 9V; I_C= 0			10	mA
h_{FE-1}	DC Current Gain	I_C= 10mA; V_{CE}= 5V	10		35	
h_{FE-2}	DC Current Gain	I_C= 1A; V_{CE}= 5V	10		35	
Switching Times; Resistive Load						
t_{on}	Turn-on Time	I_C= 6A; I_{B1}= -I_{B2}= 1.2A			1.0	μs
t_s	Storage Time				4.0	μs
t_f	Fall Time				0.8	μs